<ul> <li>UBT<sup>™</sup> (Universal Bus Transceiver) Combines D-Type Latches and D-Type</li> </ul>		CKAGE VIEW)
Flip-Flops for Operation in Transparent, Latched, or Clocked Mode		
<ul> <li>Bidirectional Interface Between GTL+ Signal Levels and LVTTL Logic Levels</li> </ul>	10EBA []2 V <sub>CC</sub> []3	63 ] 1LEAB 62 ] 1LEBA
<ul> <li>Partitioned as Two 8-Bit Transceivers With Individual Latch Timing and Output Control</li> </ul>	1A1 []4 GND []5 1A2 []6	61 ] ERC 60 ] GND 59 ] 1B1
<ul> <li>but With a Common Clock</li> <li>LVTTL Interfaces Are 5-V Tolerant</li> </ul>	1A3 [ 7 GND [ 8	58 ] 1B2 57 ] GND
<ul> <li>High-Drive GTL+ Outputs (100 mA)</li> </ul>	1A4 🛛 9	56 🛛 1B3
<ul> <li>LVTTL Outputs (-24 mA/24 mA)</li> </ul>		55 0 1B4
Variable Edge-Rate Control (ERC) Input	1A5 [ 11 GND [ 12	54 ] 1B5 53 ] GND
Selects GTL+ Rise and Fall Times for	1A6 [] 13	52 ] 1B6
Optimal Data-Transfer Rate and Signal Integrity	1A7 🖸 14	51 <b>1</b> B7
<ul> <li>I<sub>off</sub>, Power-Up 3-State, and BIAS V<sub>CC</sub> Support Live Insertion</li> </ul>	V <sub>CC</sub> [ 15 1A8 [ 16	50 ] V <sub>CC</sub> 49 ] 1B8
<ul> <li>Bus Hold on A-Port Data Inputs</li> </ul>	2A1 [ 17 GND [ 18	48 2B1 47 GND
<ul> <li>Distributed V<sub>CC</sub> and GND-Pin Configuration</li> </ul>	2A2 19	46 2B2
Minimizes High-Speed Switching Noise	2A3 🛛 20	45 <b>[</b> ] 2B3
<ul> <li>Package Option Includes Plastic Thin</li> </ul>	GND 21	44 🛛 GND
Shrink Small-Outline Package	2A4 22	43 2B4
description	2A5 23 GND 24	42 2B5 41 V <sub>REF</sub>
·	2A6 25	40 2B6
The SN74GTLPH1655 is a high-drive 16-bit	GND 26	39 🛛 GND
universal bus transceiver (UBT) that provides LVTTL-to-GTL+ and GTL+-to-LVTTL signal-level	2A7 🛛 27	<sup>38</sup> ] 2B7
translation. It is partitioned as two 8-bit		37 2B8
transceivers and allows for transparent, latched,	2A8 29 GND 30	36   BIAS V <sub>CC</sub> 35   2LEAB

**PRODUCT PREVIEW** 



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

OEC and UBT are trademarks of Texas Instruments Incorporated.

and clocked modes of data transfer similar to the

'16501 function. The device provides a

high-speed interface between cards operating at LVTTL logic levels and a backplane operating at GTL+ signal levels. High-speed (about two times faster than standard LVTTL or TTL) backplane operation is a direct result of GTLP's reduced output swing (<1 V), reduced input threshold levels, improved differential input, and output edge control (OEC™). Improved GTLP OEC circuits minimize bus settling time and have been designed and tested using several backplane models. The high drive is suitable for driving double-terminated low-impedance backplanes

PRODUCT PREVIEW information concerns products in the formative or design phase of development. Characteristic data and other specifications are design goals. Texas Instruments reserves the right to change or discontinue these products without notice.

using incident-wave switching.



Copyright © 1999, Texas Instruments Incorporated

34 2LEBA

33 OE

31

20EBA 32

20EAB

#### description (continued)

GTL+ is the Texas Instruments derivative of the Gunning transceiver logic (GTL) JEDEC standard JESD 8-3. The AC specification of the SN74GTLPH1655 is given only at the preferred higher noise margin GTL+, but the user has the flexibility of using this device at either GTL (V<sub>TT</sub> = 1.2 V and V<sub>REF</sub> = 0.8 V) or GTL+ (V<sub>TT</sub> = 1.5 V and  $V_{RFF} = 1 \text{ V}$ ) signal levels.

Normally, the B port operates at GTL or GTL+ levels, while the A-port and control inputs are compatible with LVTTL logic levels and are 5-V tolerant. V<sub>REF</sub> is the reference input voltage for the B port.

This device is fully specified for live-insertion applications using Ioff, power-up 3-state, and BIAS V<sub>CC</sub>. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict. The BIAS V<sub>CC</sub> circuitry precharges and preconditions the B-port input/output connections, preventing disturbance of active data on the backplane during card insertion or removal, and permits true live-insertion capability.

High-drive GTLP backplane interface devices feature adjustable edge-rate control (ERC). Changing the ERC input voltage between GND and V<sub>CC</sub> adjusts the B-port output rise and fall times. This allows the designer to optimize system data-transfer rate and signal integrity to the backplane load.

Active bus-hold circuitry holds unused or undriven LVTTL inputs at a valid logic state. Use of pullup or pulldown resistors with the bus-hold circuitry is not recommended.

When  $V_{CC}$  is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, the output-enable ( $\overline{OE}$ ) input should be tied to V<sub>CC</sub> through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74GTLPH1655 is characterized for operation from –40°C to 85°C.

#### functional description

The SN74GTLPH1655 is a high-drive (100 mA) 16-bit UBT containing D-type latches and D-type flip-flops for data-path operation in transparent, latched, or clocked modes and is similar to a '16501 function. The device is uniquely partitioned as two 8-bit transceivers with individual latch timing and output signals and a common clock for both transceiver words. It can replace any of the functions shown in Table 1.

FUNCTION	8 BIT	9 BIT	10 BIT	16 BIT	
Transceiver	'245, '623, '645	'863	'861	'16245, '16623	
Buffer/driver	'241, '244, '541		'827	'16241, '16244, '16541	
Latched transceiver	'543			'16543	
Latch	'373, '573	'843	'841	'16373	
Registered transceiver	'646, '652			'16646, '16652	
Flip-flop	'374, '574		'821	'16374	
SN74GTLPH1655 UBT replaces all above functions					

Table 1.	SN74GTL	PH1655 UB	T Replacemen	t Functions
			i itopiaooinon	

Data flow for each word is determined by the respective latch enables (xLEAB and xLEBA), output enables (xOEAB and xOEBA), and clock (CLK). The output enables (1OEAB, 1OEBA, 2OEAB, and 2OEBA) control byte 1 and byte 2 data for the A-to-B and B-to-A directions, respectively. Note that CLK is common to both directions and both 8-bit words. OE also is common and disables all I/O ports simultaneously.



#### functional description (continued)

For A-to-B data flow, the devices operate in the transparent mode when LEAB is high. When LEAB transitions low, the A data is latched independent of CLK high or low. If LEAB is low, the A data is registered on the CLK low-to-high transition. When OEAB is low, the outputs are active. With OEAB high, the outputs are in the high-impedance state.

Data flow for the B-to-A direction is identical, but uses OEBA, LEBA, and CLK.

#### Function Tables

FUNCTION <sup>†</sup>						
	INPUTS			OUTPUT	MODE	
OEAB	LEAB	CLK	Α	В	MODE	
Н	Х	Х	Х	Z	Isolation	
L	Н	Х	L	L	Transparent	
L	Н	Х	Н	Н	Transparent	
L	L	$\uparrow$	L	L	Registered	
L	L	$\uparrow$	Н	Н	Registered	
L	L	Н	Х	в <sub>0</sub> ‡	Previous state	
L	L	L	Х	в <sub>0</sub> ‡ в <sub>0</sub> §	Previous state	

<sup>†</sup> A-to-B data flow is shown. B-to-A flow is similar but uses OEBA, LEBA, and CLK.

<sup>‡</sup> Output level before the indicated steady-state input conditions were established, provided that CLK was high before LEAB went low

§ Output level before the indicated steady-state input conditions were established

INPUTS			OUTPUTS		
OE	OEAB	OEBA	A PORT	<b>B PORT</b>	
L	L	L	Active	Active	
L	L	Н	Z	Active	
L	Н	L	Active	Z	
L	Н	Н	Z	Z	
Н	Х	Х	Z	Z	

#### **OUTPUT ENABLE**

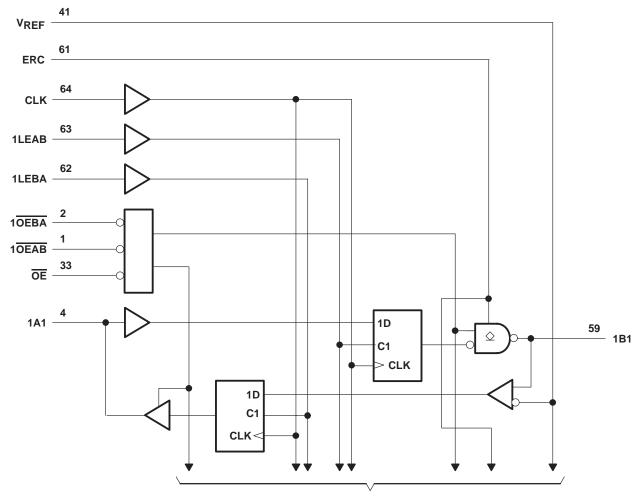
#### **B-PORT EDGE-RATE CONTROL (ERC)**

	INPU	JT ERC	OUTPUT
	LOGIC LEVEL	NOMINAL VOLTAGE	B-PORT EDGE RATE
Γ	Н	VCC	Slow
L	L	GND	Fast



SCES294 - OCTOBER 1999

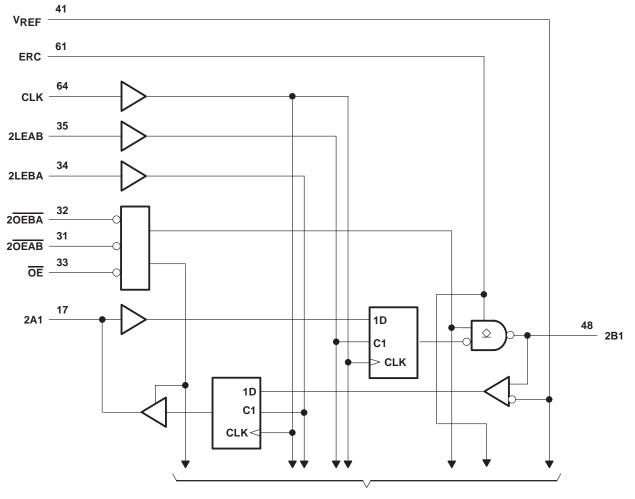
### logic diagram (positive logic)



**To Seven Other Channels** 







logic diagram (positive logic) (continued)

To Seven Other Channels

**PRODUCT PREVIEW** 



SCES294 - OCTOBER 1999

#### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage range, V <sub>CC</sub> and BIAS V <sub>CC</sub> Input voltage range, V <sub>I</sub> (see Note 1):A-port and control inputs B port, ERC, and V <sub>RFF</sub>	–0.5 V to 7 V
Voltage range applied to any output in the high-impedance or power-off state, V <sub>O</sub> (see Note 1): A port	–0.5 V to 7 V
Voltage range applied to any output in the high or low state, V <sub>O</sub> (see Note 1): A port	–0.5 V to 4.6 V
Current into any output in the low state, I <sub>O</sub> : A port B port	
Current into any A-port output in the high state, I <sub>O</sub> (see Note 2)	48 mA
Continuous current through each V <sub>CC</sub> or GND	
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)	–50 mA
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)	
Package thermal impedance, $\theta_{JA}$ (see Note 3)	55°C/W
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. This current flows only when the output is in the high state and  $V_O > V_{CC}$ .

3. The package thermal impedance is calculated in accordance with JESD 51.



SCES294 – OCTOBER 1999

#### recommended operating conditions (see Notes 4 through 6)

			MIN	NOM	MAX	UNIT	
V <sub>CC</sub> , BIAS V <sub>CC</sub>	Supply voltage		3.15	3.3	3.45	V	
	Terreis eties valte es	GTL	1.14	1.2	1.26	v	
VTT	Termination voltage	GTL+	1.35	1.5	1.65		
M	Supply veltage	GTL	0.74	0.8	0.87	v	
VREF	Supply voltage	GTL+	0.87	1	1.1	1 <sup>v</sup>	
\ <i>\</i> .		B port			VTT	v	
VI	Input voltage	Except B port			VCC		
	High-level input voltage	B port	V <sub>REF</sub> +0.05				
VIH		ERC	V <sub>CC</sub> -0.6	Vcc		V	
		Except B port and ERC	2			1	
		B port			V <sub>REF</sub> -0.05		
VIL	Low-level input voltage	ERC		GND	0.6	V	
		Except B port and ERC			0.8	1	
IIK	Input clamp current	•			-18	mA	
IOH	High-level output current	A port			-24	mA	
		A port			24		
IOL	Low-level output current	B port	1		100	mA	
T <sub>A</sub>	Operating free-air temperature	•	-40		85	°C	

NOTES: 4. All unused control and B-port inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

5. Normal connection sequence is GND first, BIAS  $V_{CC}$  = 3.3 V second, and  $V_{CC}$  = 3.3 V, I/O, control inputs,  $V_{TT}$  and  $V_{REF}$  (any order) last. However, if the B-port I/O precharge is not required, the acceptable connection sequence is GND first and  $V_{CC}$  = 3.3 V, BIAS  $V_{CC}$  = 3.3 V, I/O, control inputs,  $V_{TT}$  and  $V_{REF}$  (any order) last. When  $V_{CC}$  is connected, the BIAS  $V_{CC}$  circuitry is disabled.

 V<sub>TT</sub> and R<sub>TT</sub> can be adjusted to accommodate backplane impedances as long as they do not exceed the DC absolute I<sub>OL</sub> ratings. Similarly, V<sub>REF</sub> can be adjusted to optimize noise margins, but normally is 2/3 V<sub>TT</sub>.



SCES294 - OCTOBER 1999

#### electrical characteristics over recommended operating free-air temperature range for GTL+ (unless otherwise noted)

PARAMETER		TEST CONDITIONS			TYP†	MAX	UNIT	
VIK		V <sub>CC</sub> = 3.15 V,	I <sub>I</sub> = -18 mA			-1.2	V	
			I <sub>OH</sub> = –100 μA	V <sub>CC</sub> -0.2				
VOH	A port		I <sub>OH</sub> = -12 mA	2.4			V	
		V <sub>CC</sub> = 3.15 V	I <sub>OH</sub> = -24 mA	2				
		V <sub>CC</sub> = 3.15 V to 3.45 V,	I <sub>OL</sub> = 100 μA			0.2		
	A port	V <sub>CC</sub> = 3.15 V	I <sub>OL</sub> = 12 mA			0.4		
Val		VCC = 3.15 V	I <sub>OL</sub> = 24 mA			0.5	V	
VOL			I <sub>OL</sub> = 10 mA			0.2	v	
	B port	V <sub>CC</sub> = 3.15 V	I <sub>OL</sub> = 64 mA			0.4		
			I <sub>OL</sub> = 100 mA			0.55		
II <sup>‡</sup> A-po	B port	V <sub>CC</sub> = 3.45 V,	$V_{I} = 0$ to 1.5 V			±10		
	A-port and control inputs	V <sub>CC</sub> = 3.45 V	VI = 0  or  VCC			±10	μA	
			V <sub>I</sub> = 5.5 V			±20		
I <sub>BHL</sub> §	A port	V <sub>CC</sub> = 3.15 V,	V <sub>I</sub> = 0.8 V	75			μΑ	
IBHH	A port	V <sub>CC</sub> = 3.15 V,	V <sub>I</sub> = 2 V	-75			μΑ	
IBHLO <sup>#</sup>	A port	V <sub>CC</sub> = 3.45 V,	$V_{I} = 0$ to $V_{CC}$			500	μΑ	
Івнно	A port	V <sub>CC</sub> = 3.45 V,	$V_I = 0$ to $V_{CC}$			-500	μA	
		V <sub>CC</sub> = 3.45 V, I <sub>O</sub> = 0,	Outputs high			40		
ICC	A or B port	$V_I$ (A-port or control input) = $V_{CC}$ or GND	Outputs low			40	mA	
		V <sub>I</sub> (B port) = V <sub>TT</sub> or GND	Outputs disabled			40		
∇ICC☆		$V_{CC}$ = 3.45 V, One A-port or control input at Other A-port or control inputs at $V_{CC}$ or GNI				1.5	mA	
Ci	Control inputs	V <sub>I</sub> = 3.15 V or 0					pF	
<u>C.</u>	A port	V <sub>O</sub> = 3.15 V or 0						
Cio	B port	V <sub>O</sub> = 1.5 V or 0					pF	

<sup>†</sup> All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> =  $25^{\circ}$ C.

<sup>‡</sup> For I/O ports, the parameter I<sub>1</sub> includes the off-state output leakage current.

§ The bus-hold circuit can sink at least the minimum low sustaining current at VIL max. IBHL should be measured after lowering VIN to GND and then raising it to VIL max.

The bus-hold circuit can source at least the minimum high sustaining current at VIHmin. IBHH should be measured after raising VIN to VCC and then lowering it to VIHmin.

# An external driver must source at least IBHLO to switch this node from low to high.

An external driver must sink at least IBHHO to switch this node from high to low.

 $\star$ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V<sub>CC</sub> or GND.

#### live-insertion specifications for A port over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS			MAX	UNIT
l <sub>off</sub>	$V_{CC} = 0,$	BIAS $V_{CC} = 0$ ,	$V_{I}$ or $V_{O}$ = 0 to 5.5 V		100	μΑ
IOZPU	$V_{CC} = 0$ to 1.5 V,	$V_{O}$ = 0.5 V to 3 V,	OE = 0		±100	μA
IOZPD	V <sub>CC</sub> = 1.5 V to 0,	$V_{O}$ = 0.5 V to 3 V,	OE = 0		±100	μΑ



#### live-insertion specifications for B port over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS				UNIT
l <sub>off</sub>	$V_{CC} = 0,$	BIAS $V_{CC} = 0$ ,	$V_{I}$ or $V_{O}$ = 0 to 1.5 V		100	μA
IOZPU	$V_{CC} = 0$ to 1.5 V,	$V_{O} = 0.5 V$ to 1.5 V,	$\overline{OE} = 0$		±100	μA
IOZPD	$V_{CC} = 1.5 V \text{ to } 0,$	$V_{O} = 0.5 V$ to 1.5 V,	$\overline{OE} = 0$		±100	μA
	V <sub>CC</sub> = 0 to 3.15 V	BIAS $V_{CC}$ = 3.15 V to 3.45 V,	$V_{O}$ (B port) = 0 to 1.5 V		5	mA
ICC (BIAS VCC)	V <sub>CC</sub> = 3.15 V to 3.45 V				10	μA
VO	$V_{CC} = 0,$	BIAS $V_{CC}$ = 3.3 V		0.95	1.05	V
IO	$V_{CC} = 0,$	BIAS V <sub>CC</sub> = $3.15$ V to $3.45$ V,	V <sub>O</sub> (B port) = 0.6 V	-1		μA

# timing requirements over recommended ranges of supply voltage and operating free-air temperature, $V_{TT}$ = 1.5 V and $V_{REF}$ = 1 V for GTL+ (unless otherwise noted)

			MIN	MAX	UNIT
fclock	Clock frequency				MHz
+	Pulse duration	LEAB or LEBA high			ns
tw		CLK high or low			115
	A before CLK				
•	Setup time	B before CLK			
t <sub>su</sub>	Setup time	A before LEAB $\downarrow$ , CLK = don't care			ns
		B before LEBA $\downarrow$ , CLK = don't care			
		A after CLK			
	Hold time	B after CLK			
th		A after LEAB $\downarrow$ , CLK = don't care			ns
		B after LEBA↓, CLK = don't care			



SCES294 – OCTOBER 1999

switching characteristics over recommended ranges of supply voltage and operating free-air temperature,  $V_{TT}$  = 1.5 V and  $V_{REF}$  = 1 V for GTL+ (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE <sup>†</sup>	MIN TYP‡	МАХ	UNIT
f <sub>max</sub>						MHz
<sup>t</sup> pd	А	В	Slow			ns
			Fast			
	LEAB	В	Slow			
			Fast			
	CLK	В	Slow			
			Fast			
<sup>t</sup> en	OE	В	Slow			ns
<sup>t</sup> dis						
<sup>t</sup> en	OE	В	Fast			ns
<sup>t</sup> dis	UE		1 431			
t <sub>en</sub>	OEAB	В	Slow			ns
<sup>t</sup> dis						
<sup>t</sup> en	OEAB	В	Fast			ns
<sup>t</sup> dis						
tr	Rise time, B outputs (0.6 V to 1.3 V)		Slow			ns
			Fast			
t <sub>f</sub>	Fall time, B outputs (1.3 V to 0.6 V)		Slow			ns
			Fast			
<sup>t</sup> pd	В					ns
	LEBA	A				
	CLK					
t <sub>en</sub>	OE	A				ns
<sup>t</sup> dis						
t <sub>en</sub>	OEBA	А				200
<sup>t</sup> dis						ns

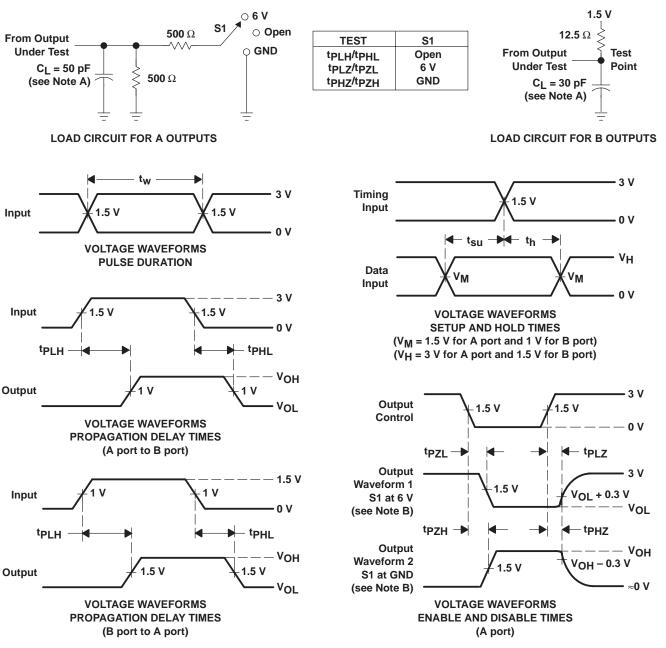
<sup>†</sup>Slow (ERC =  $V_{CC}$ ) and Fast (ERC = GND)

<sup>‡</sup> All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> =  $25^{\circ}$ C.



SCES294 - OCTOBER 1999

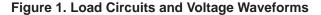




NOTES: A. C<sub>I</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>Q</sub> = 50  $\Omega$ , slew rate  $\leq$  1 V/ns.

D. The outputs are measured one at a time with one transition per measurement.





SCES294 - OCTOBER 1999

#### DISTRIBUTED-LOAD BACKPLANE SWITCHING CHARACTERISTICS

This data sheet is specified for and tested to the lump load shown in Figure 1. However, the designer probably uses this GTLP device in a distributed load like that shown in Figure 2, in which actual B-port backplane switching characteristics are different. Therefore, the device is modeled as shown in Figure 3, which very closely matches the results obtained using Figure 2. Switching characteristics based on Figure 3 more closely match actual backplane design requirements.

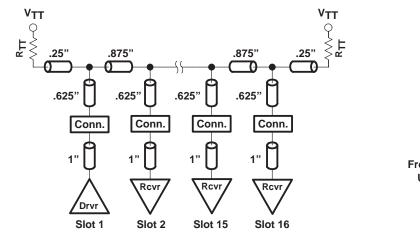


Figure 2. Test Backplane Model

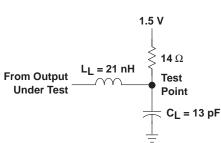


Figure 3. Distributed-Load Circuit for B Outputs

switching characteristics over recommended ranges of supply voltage and operating free-air	
temperature, V <sub>TT</sub> = 1.5 V and V <sub>REF</sub> = 1 V for GTL+ (see Figure 3)	

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE <sup>†</sup>	MIN TYP <sup>‡</sup>	МАХ	υΝΙΤ
f <sub>max</sub>						MHz
<sup>t</sup> pd	А	В	Slow			ns
			Fast			
	LEAB	В	Slow			
			Fast			
	CLK	В	Slow			
			Fast			
ten	ŌĒ	В	Slow			ns
<sup>t</sup> dis						
t <sub>en</sub>	OE	В	Fast			ns
<sup>t</sup> dis						
t <sub>en</sub>	OEAB	В	Slow			ns
<sup>t</sup> dis						
t <sub>en</sub>	OEAB	В	Fast			ns
<sup>t</sup> dis						
t <sub>r</sub>	Rise time, B outputs (0.6 V to 1.3 V)		Slow			ns
			Fast			
tf	Fall time, B outputs (1.3 V to 0.6 V)		Slow			ns
			Fast			

<sup>†</sup>Slow (ERC =  $V_{CC}$ ) and Fast (ERC = GND)

<sup>‡</sup> All typical values are at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C.



#### **IMPORTANT NOTICE**

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1999, Texas Instruments Incorporated